



CMKT3904 NPN/NPN
 CMKT3906 PNP/PNP
 CMKT3946 NPN/PNP

**SURFACE MOUNT ULTRAmi™
 DUAL SMALL SIGNAL SILICON
 SWITCHING TRANSISTORS**

ULTRAmi™



SOT-363 CASE

Central™

Semiconductor Corp.

DESCRIPTION:

The Central Semiconductor CMKT3904 (two single NPN), CMKT3906 (two single PNP), and CMKT3946 (one each NPN and PNP complementary) are combinations of transistors in a space saving SOT-363 ULTRAmi™ package, designed for small signal general purpose amplifier and switching applications.

CMKT3904 MARKING CODE: K04
CMKT3906 MARKING CODE: K06
CMKT3946 MARKING CODE: K46

FEATURES:

- ULTRAmi™ space saving package
- Two NPN (3904) or Two PNP (3906) Transistors in a single package

- One NPN (3904) and one PNP (3906) complementary Transistor in a single package

MAXIMUM RATINGS: (T_A=25°C)

Collector-Base Voltage
 Collector-Emitter Voltage
 Emitter-Base Voltage
 Continuous Collector Current
 Power Dissipation
 Operating and Storage Junction Temperature
 Thermal Resistance

SYMBOL	<u>NPN</u>	<u>PNP</u>	UNITS
V _{CB0}	60	40	V
V _{CEO}	40	40	V
V _{EBO}	6.0	5.0	V
I _C		200	mA
P _D		350	mW
T _J , T _{stg}	-65 to +150		°C
θ _{JA}	357		°C/W

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	<u>NPN</u>		<u>PNP</u>		UNITS
		MIN	MAX	MIN	MAX	
I _{CEV}	V _{CE} =30V, V _{EB} =3.0V	-	50	-	50	nA
I _{BL}	V _{CE} =30V, V _{EB} =3.0V	-	50	-	-	nA
BV _{CB0}	I _C =10μA	60	-	40	-	nA
BV _{CEO}	I _C =1.0mA	40	-	40	-	nA
BV _{EBO}	I _E =10μA	6.0	-	5.0	-	nA
V _{CE(SAT)}	I _C =10mA, I _B =1.0mA	-	0.20	-	0.25	V
V _{CE(SAT)}	I _C =50mA, I _B =5.0mA	-	0.30	-	0.40	V
V _{BE(SAT)}	I _C =10mA, I _B =1.0mA	0.65	0.85	0.65	0.85	V
V _{BE(SAT)}	I _C =50mA, I _B =5.0mA	-	0.95	-	0.95	V
h _{FE}	V _{CE} =1.0V, I _C =0.1mA	40	-	60	-	
h _{FE}	V _{CE} =1.0V, I _C =1.0mA	70	-	80	-	
h _{FE}	V _{CE} =1.0V, I _C =10mA	100	300	100	300	
h _{FE}	V _{CE} =1.0V, I _C =50mA	60	-	60	-	
h _{FE}	V _{CE} =1.0V, I _C =100mA	30	-	30	-	
f _T	V _{CE} =20V, I _C =10mA, f=100MHz	300	-	250	-	MHz
C _{ob}	V _{CB} =5.0V, I _E =0, f=1.0MHz	-	4.0	-	4.5	pF
C _{ib}	V _{BE} =0.5V, I _C =0, f=1.0MHz	-	8.0	-	10	pF

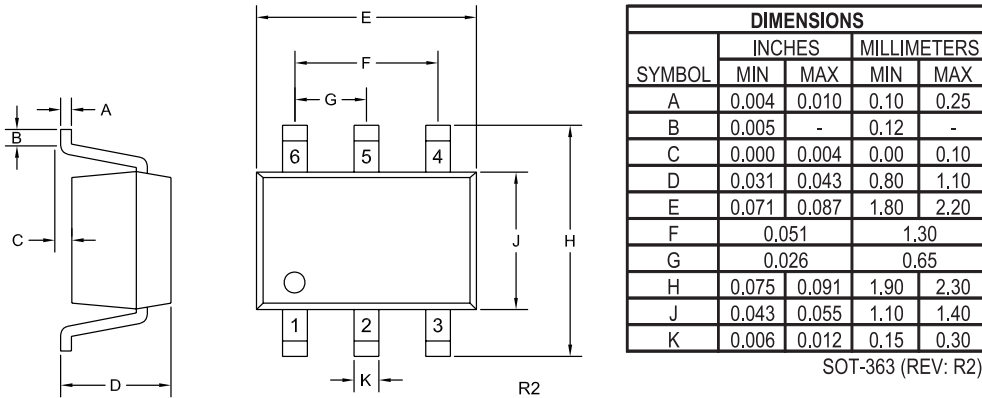
R3 (21-November 2008)

SURFACE MOUNT ULTRAmiTM
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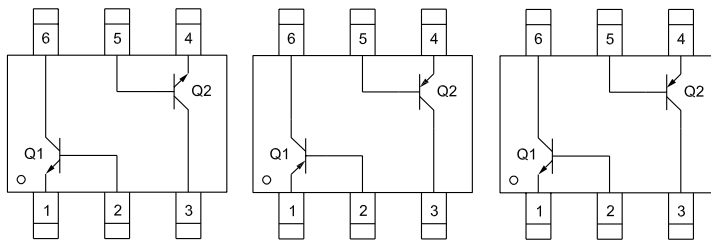
ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	NPN		PNP		UNITS
		MIN	MAX	MIN	MAX	
h_{ie}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	1.0	10	2.0	12	$k\Omega$
h_{re}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	0.5	8.0	0.1	10	$\times 10^{-4}$
h_{fe}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	100	400	100	400	
h_{oe}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	1.0	40	3.0	60	μS
NF	$V_{CE}=5.0\text{V}, I_C=100\mu\text{A}, R_S=1.0\text{k}\Omega, f=10\text{Hz to } 15.7\text{kHz}$	-	5.0	-	4.0	dB
t_d	$V_{CC}=3.0\text{V}, V_{BE}=0.5\text{V}, I_C=10\text{mA}, I_{B1}=1.0\text{mA}$	-	35	-	35	ns
t_r	$V_{CC}=3.0\text{V}, V_{BE}=0.5\text{V}, I_C=10\text{mA}, I_{B1}=1.0\text{mA}$	-	35	-	35	ns
t_s	$V_{CC}=3.0\text{V}, I_C=10\text{mA}, I_{B1}=I_{B2}=1.0\text{mA}$	-	200	-	225	ns
t_f	$V_{CC}=3.0\text{V}, I_C=10\text{mA}, I_{B1}=I_{B2}=1.0\text{mA}$	-	50	-	75	ns

SOT-363 CASE - MECHANICAL OUTLINE



PIN CONFIGURATIONS



CMKT3904
(NPN/NPN)

MARKING CODE: K04

CMKT3906
(PNP/PNP)

MARKING CODE: K06

CMKT3946
(NPN/PNP)

MARKING CODE: K46

LEAD CODES:

- 1) EMITTER Q1
- 2) BASE Q1
- 3) COLLECTOR Q2
- 4) EMITTER Q2
- 5) BASE Q2
- 6) COLLECTOR Q1